

isc Silicon NPN RF Transistor

2SC2759

DESCRIPTION

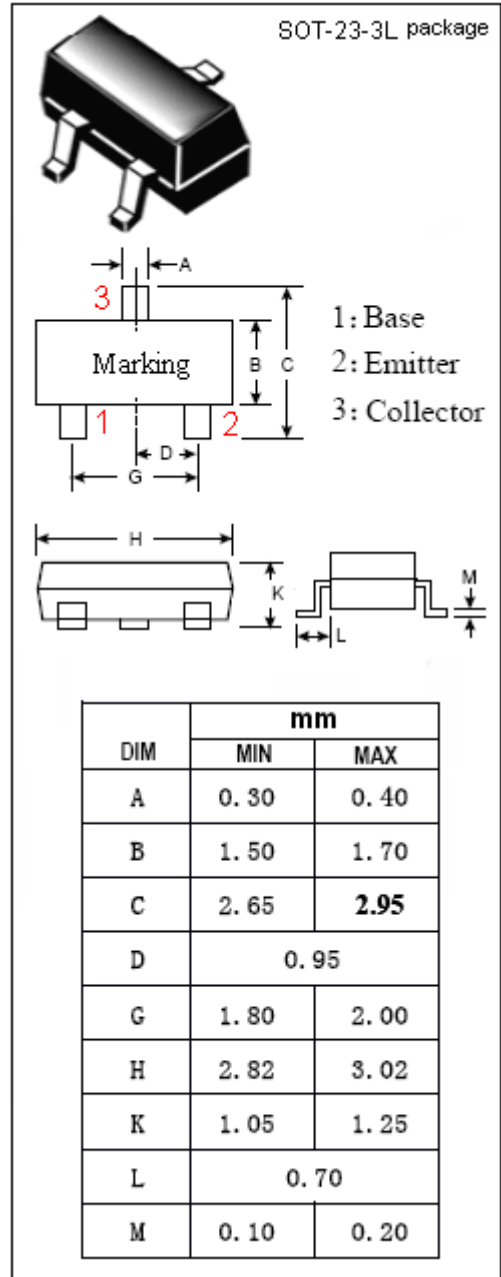
- Low Noise
 - High Conversion Gain
- $G_{cb} = 12.5\text{dB TYP. @ } I_E = -5\text{mA, } V_{CB} = 10\text{V}$

APPLICATIONS

- Designed for use in VHF RF amplifier, local oscillator, mixer.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	14	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current-Continuous	50	mA
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	0.15	W
T_J	Junction Temperature	125	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~125	$^\circ\text{C}$



isc Silicon NPN RF Transistor**2SC2759****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	$V_{CB}= 15\text{V}; I_E= 0$			0.1	μA
h_{FE}	DC Current Gain	$I_C= 5\text{mA}; V_{CE}= 10\text{V}$	40		180	
f_T	Current-Gain—Bandwidth Product	$I_C= 5\text{mA}; V_{CE}= 10\text{V}$	1.5	2.0		GHz
C_{OB}	Output Capacitance	$I_E= 0; V_{CB}= 10\text{V}; f= 1.0\text{MHz}$		1.0	1.3	pF
G_{cb}	Conversion Gain	$I_E= -5\text{mA}; V_{CB}= 10\text{V}; f= 900\text{MHz};$ $f_{OSC}= 935\text{MHz}, 115\text{ dB } \mu\text{V}$	10	12.5		dB

◆ **h_{FE} Classification**

Marking	U21	U22	U23
h_{FE}	40-80	60-120	90-180